

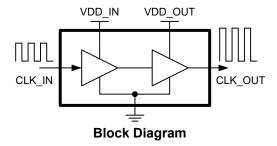
CDCBT1001 1.2V to 3.3 V Clock Buffer and Level Translator

1 Features

- Low additive jitter and phase noise:
 - 0.8ps maximum 12kHz to 5MHz additive RMS iitter ($f_{out} = 24MHz$)
 - -120dBc/Hz maximum phase noise at 1kHz offset ($f_{out} = 24MHz$)
 - 148dBc/Hz maximum phase noise floor (f_{out} = 24MHz, f_{offset} ≥ 1MHz)
- 5ns 20% to 80% rise/fall time
- 10ns propagation delay
- Low current consumption
- -40°C to 85°C operating temperature range
- Flexible output from operational frequency

2 Applications

- FPGA/processor clock buffering/level translation in personal electronics
- 1.2V clock buffer and level translator in servers and add-in cards



3 Description

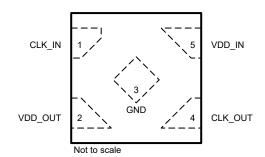
The CDCBT1001 is a 1.2V to 3.3V clock buffer and level translator. The VDD IN pin supply voltage defines the input LVCMOS clock level. The VDD OUT pin supply voltage defines the output LVCMOS clock level. VDD IN = 1.2V, 1.8V, 2.5V, or $3.3V \pm 10\%$. VDD OUT = 1.2V, 1.8V, 2.5V, or $3.3V \pm 10\%$.

The 12kHz to 5MHz additive RMS jitter at 24MHz is less than 0.8ps.

Package Information

PART NUMBER	PACKAGE ⁽¹⁾	PACKAGE SIZE ⁽²⁾
CDCBT1001	DPW (X2SON, 5)	0.80mm × 0.80mm

- For more information, see Section 10.
- The package size (length × width) is a nominal value and includes pins, where applicable.



Pin Configuration



Table of Contents

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4 Pin Configuration and Functions

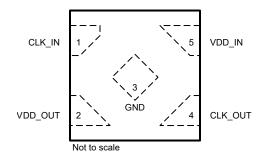


Figure 4-1. DPW Package 5-Pin X2SON Transparent Top View

Table 4-1. Pin Functions

PIN		TYPE ⁽¹⁾	DESCRIPTION
NAME	NO.	IIFE(/	DESCRIPTION
CLK_IN	1	I	Clock input. LVCMOS input clock is injected into this pin. The acceptable LVCMOS voltage level is defined by VDD_IN.
CLK_OUT	4	0	Clock output. This pin outputs LVCMOS clock. The output LVCMOS voltage level is defined by VDD_OUT
VDD_IN	5	Р	Input supply voltage. VDD_IN can be 1.2V, 1.8V, 2.5V, or 3.3V ± 10%.
VDD_OUT	2	Р	Output supply voltage. VDD_OUT can be 1.2V, 1.8V, 2.5V, or 3.3V ± 10%.
GND	3	G	Ground

⁽¹⁾ I = Input, O = Output, P = Power, G = Ground



5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

		MIN	MAX	UNIT
VDD_IN	VDD_IN supply voltage	-0.5	3.63	V
VDD_OUT	VDD_OUT supply voltage	-0.5	3.63	V
VI	Input voltage ⁽²⁾	-0.5	3.63	V
V	Voltage applied to the output in the high-impedance or power-off state ⁽²⁾	-0.5	3.63	V
Vo	Voltage applied to the output in the high or low state ^{(2) (3)}	-0.5	VDD_OUT + 0.2	V
I _{IK}	Input clamp current, V _I < 0		-50	mA
I _{OK}	Output clamp current, V _O < 0		-50	mA
	Continuous output current	-50	50	mA
Io	Continuous current through VDD_OUT or GND	-50	50	mA
Io	Continuous current through VDD_IN	-10	10	mA
TJ	Junction temperature	-40	150	°C
T _{stg}	Storage temperature	-65	150	°C

⁽¹⁾ Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute Maximum Ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If used outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.

5.2 ESD Ratings

			VALUE	UNIT	OWNER
V	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/ JEDEC JS-001, all pins ⁽¹⁾	±2000	V	
V _(ESD)	Liectiostatic discriarge	Charged device model (CDM), per JEDEC specification JS-002, all pins ⁽²⁾	±1000	V	

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

5.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
VDD_IN	Input supply voltage	1.08	1.2	1.32	V
VDD_IN	Input supply voltage	1.62	1.8	1.98	V
VDD_IN	Input supply voltage	2.25	2.5	2.75	V
VDD_IN	Input supply voltage	2.97	3.3	3.63	V
VDD_OUT	Output supply voltage	1.08	1.2	1.32	V
VDD_OUT	Output supply voltage	1.62	1.8	1.98	V
VDD_OUT	Output supply voltage	2.25	2.5	2.75	V
VDD_OUT	Output supply voltage	2.97	3.3	3.63	V
T _A	Ambient temperature	-40		85	°C

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⁽²⁾ The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.

⁽³⁾ The output positive-voltage rating may be exceeded up to 2.25 V maximum if the output current ratings are observed.

⁽²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



5.4 Thermal Information

THERMAL METRIC ⁽¹⁾		CDCBT1001	
		DPW (X2SON)	UNIT
		5 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	462.7	°C/W
R ₀ JC(top)	Junction-to-case (top) thermal resistance	227.7	°C/W
R _{θJB}	Junction-to-board thermal resistance	326.5	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	33.8	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	325.1	°C/W

⁽¹⁾ For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application note.

5.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

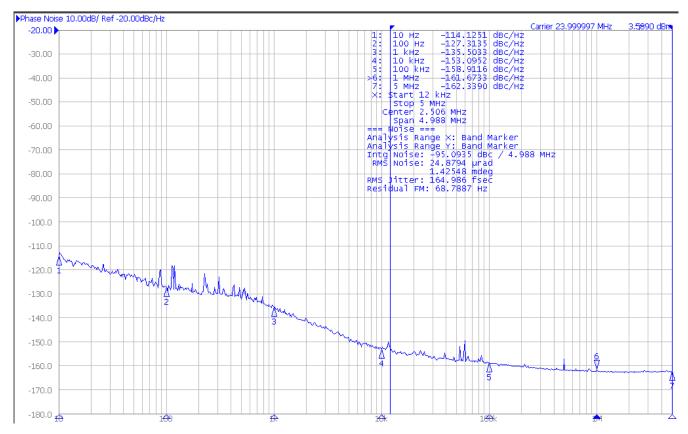
	PARAMETER	TEST CONDITIONS	MIN	TYP MAX	UNIT
POWER S	SUPPLY CHARACTERISTICS				
Current consumption on		Both input and output clocks are toggling. 2 pF load termination. f ₀ = 12 MHz.		35	μΑ
IDD_IN	VDD_IN	Both input and output clocks are toggling. 2 pF load termination. f ₀ = 24 MHz.		60	μΑ
Current consumption on		Both input and output clocks are toggling. 2 pF load termination. f ₀ = 12 MHz.		500	μΑ
IDD_OUT	VDD_OUT	Both input and output clocks are toggling. 2 pF load termination. $f_0 = 24$ MHz.		1000	μΑ
CLOCK IN	IPUT CHARACTERISTICS				
f_0	Operating frequency	VDD_OUT = 3.3V	DC	75	MHz
f_0	Operating frequency	VDD_OUT = 2.5V	DC	75	MHz
f_0	Operating frequency	VDD_OUT = 1.8V	DC	75	MHz
f_0	Operating frequency	VDD_IN = 1.2V, VDD_OUT = 1.2V	DC	50	MHz
f ₀	Operating frequency	VDD_IN = 1.8V, VDD_OUT = 1.2V	DC	75	MHz
f ₀	Operating frequency	VDD_IN = 2.5V, VDD_OUT = 1.2V	24	75	MHz
f_0	Operating frequency	VDD_IN = 3.3V, VDD_OUT = 1.2V	24	75	MHz
I _{IN_LEAK}	Input leakage current		-8	8	μA
V _{IH}	Input voltage high		VDD_IN x 0.8		V
V _{IL}	Input voltage low			VDD_IN x 0.2	V
Δν/Δt	Input edge rate		0.01		V/ns
Cı	Input capacitance			2	pF
t _{startup}	Time after power supply exceeds 0.5 V before applying input clock, to provide glitchless output			225	μs
CLOCK O	UTPUT CHARACTERISTICS				
V _{OH}	Output voltage high	V _I = V _{IH} , I _{OH} = -100 μA, VDD_OUT = 1.62-1.98 V	VDD_OUT - 0.1		V
V _{OH}	Output voltage high	V _I = V _{IH} , I _{OH} = -8 mA, VDD_OUT = 1.62 V	1.2		V
V _{OL}	Output voltage low	V _I = V _{IL} , I _{OL} = 100 μA, VDD_OUT = 1.62-1.98 V		0.1	V
V _{OL}	Output voltage low	V _I = V _{IL} , I _{OL} = 8 mA, VDD_OUT = 1.62 V		0.45	V



over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
ODC	Output duty cycle	Input duty cycle = 45% - 55%, input slew rate \geq 0.2 V/ns, V _{IL} \leq 0.15 x VDD_IN, V _{IH} \geq 0.85 x VDD_IN, V _{IH} - V _{IL} \geq 850 mVpp	40		60	%
ODC	Output duty cycle	Input duty cycle = 45% - 55% , input slew rate ≥ 0.2 V/ns, V _{IL} ≤ 0.2 x VDD_IN, V _{IH} \geq 0.8 x VDD_IN, V _{IH} - V _{IL} ≥ 850 mVpp	37		63	%
t _R , t _F	Clock output rise/fall time	20% to 80%, 2 pF load capacitance			3	ns
t _{PD}	Input-to-output propagation delay	Input slew rate \geq 0.2 V/ns, V _{IL} \leq 0.2 x VDD_IN, V _{IH} \geq 0.8 x VDD_IN, V _{IH} - V _{IL} \geq 850 mVpp			10	ns
R _{out}	Output impedance			34		Ω
CLOCK	OUTPUT PERFORMANCE					
RJ _{RMS} -	12 kHz to 5 MHz additive RMS random jitter	f_0 =24 MHz, input slew rate \geq 0.2 V/ns, V _{IH} - V _{IL} \geq 850 mVpp			0.8	ps
PN ₁₀	Output phase noise at 10 Hz	f_0 =24 MHz, input phase noise = -104 dBc/Hz, input slew rate \geq 0.2 V/ns, V _{IH} - V _{IL} \geq 850 mVpp			-100	dBc/Hz
PN ₁₀₀	Output phase noise at 100 Hz	f_0 =24 MHz, input phase noise = -127 dBc/Hz, input slew rate \geq 0.2 V/ns, V _{IH} - V _{IL} \geq 850 mVpp			-110	dBc/Hz
PN _{1k}	Output phase noise at 1 kHz	f_0 =24 MHz, input phase noise = -137 dBc/Hz, input slew rate \geq 0.2 V/ns, V _{IH} - V _{IL} \geq 850 mVpp			-120	dBc/Hz
PN _{10k}	Output phase noise at 10 kHz	f_0 =24 MHz, input phase noise = -159 dBc/Hz, input slew rate \geq 0.2 V/ns, V _{IH} - V _{IL} \geq 850 mVpp			-130	dBc/Hz
PN _{100k}	Output phase noise at 100 kHz	f_0 =24 MHz, input phase noise = -164 dBc/Hz, input slew rate \geq 0.2 V/ns, V _{IH} - V _{IL} \geq 850 mVpp			-140	dBc/Hz
PN _{1M}	Output phase noise at 1 MHz	f_0 =24 MHz, input phase noise = -166 dBc/Hz, input slew rate \geq 0.2 V/ns, V _{IH} - V _{IL} \geq 850 mVpp			-148	dBc/Hz
PN _{5M}	Output phase noise at 5 MHz	f_0 =24 MHz, input phase noise = -165 dBc/Hz, input slew rate \geq 0.2 V/ns, V _{IH} - V _{IL} \geq 850 mVpp			-148	dBc/Hz

5.6 Typical Characteristics



 $VDD_IN = 1.2V, VDD_OUT = 1.8V, T_A = 25^{\circ}C,$

Input phase noise as specified in Electrical Characteristics table

Figure 5-1. 24MHz Phase Noise



6 Detailed Description

6.1 Overview

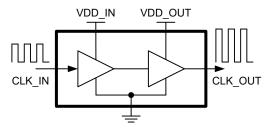
The CDCBT1001 is a single-channel, 1.2V to 1.8V, 3.3V and 1.8V to 3.3V clock buffer and level translator. VDD IN defines input LVCMOS clock level and VDD OUT defines output LVCMOS clock level.

Table 6-1 highlights the flexibility of the device.

Table 6-1. Input and Output LVCMOS Level Translations With Operating Frequency Range

	VDD_OUT = 1.2V ± 10%	VDD_OUT = 1.8V ± 10%	VDD_OUT = 2.5V ± 10%	VDD_OUT = 3.3V ± 10%
VDD_IN = 1.2V ± 10%	DC - 50MHz	DC - 75MHz	DC - 75MHz	DC - 75MHz
VDD_IN = 1.8V ± 10%	DC - 75MHz	DC - 75MHz	DC - 75MHz	DC - 75MHz
VDD_IN = 2.5V ± 10%	24MHz - 75MHz	DC - 75MHz	DC - 75MHz	DC - 75MHz
VDD_IN = 3.3V ± 10%	24MHz - 75MHz	DC - 75MHz	DC - 75MHz	DC - 75MHz

6.2 Functional Block Diagram



6.3 Feature Description

6.3.1 Power Down Tolerant Input

The device can have a clock signal on the input pin when the chip is powered down.

6.3.2 Up Conversion

The device supports 1.2V to 1.8V, 1.2V to 3.3V, and 1.8V to 3.3V up conversion.

6.4 Device Functional Modes

The device has one mode of operation that applies when operated within the *Recommended Operating Conditions*.

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7 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

7.1 Application Information

The CDCBT1001 device can be used in level-translation applications for interfacing between devices or systems that are operating at different interface voltages.

7.2 Typical Applications

7.2.1 Processor Clock Up Translation

Figure 7-1 shows an example of CDCBT1001 being used in a clock level shifting application.

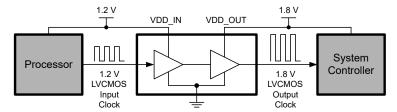


Figure 7-1. Processor Clock Up Translation Application

7.2.1.1 Design Requirements

For this design example, use the parameters shown in Table 7-1.

Table 7-1. Design Parameters

	9
DESIGN PARAMETER	EXAMPLE VALUE
Input voltage supply	1.2V
Output voltage supply	1.8V

7.2.1.2 Detailed Design Procedure

To begin the design process, determine the following:

- Input clock
 - The supply voltage on VDD IN determines the input clock voltage range.
 - For a valid logic-high, the high level clock input must exceed V_{IH} spec. For a valid logic-low, the low level clock input must be below V_{II} .
 - Some specifications such as duty cycle and phase noise have additional requirements for V_{IH}, V_{IL}, input swing and input slew rate. Refer to the test conditions column in the *Electrical Characteristics* table.
- · Output clock
 - The supply voltage on VDD OUT determines the output clock voltage range.

7.2.1.3 Application Curve

Figure 5-1 listed in the *Typical Characteristics* section can also be used as an application curve for the *Processor Clock Up Translation* application example.

Table 7-2. Table of Graphs

TITLE	FIGURE			
24MHz Phase Noise	Figure 5-1			

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7.3 Power Supply Recommendations

TI recommends to place a 0.1µF bypass capacitor on each VDD pin.

7.4 Layout

7.4.1 Layout Guidelines

To provide reliability of the device, follow the common printed-circuit board layout guidelines listed below:

- · Use bypass capacitors on power supplies.
- · Use short trace lengths to avoid excessive loading.

Figure 7-2 shows an example layout for the DPW (X2SON-5) package. This example layout includes two 0402 (metric) capacitors, and uses the measurements listed in the package outline drawing appended to the end of this data sheet. A via of diameter 0.1mm (3.973mil) is placed directly in the center of the device. This via can be used to trace out the center pin connection through another board layer, or the via can be left out of the layout.

7.4.2 Layout Example

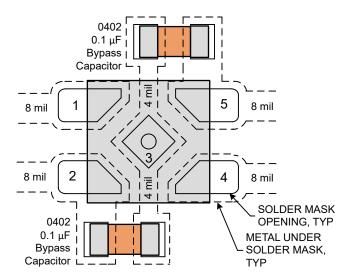


Figure 7-2. Example Layout for the DPW (X2SON-5) Package

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8 Device and Documentation Support

8.1 Documentation Support

8.1.1 Related Documentation

For related documentation see the following:

- Texas Instruments, Implications of Slow or Floating CMOS Inputs application note
- Texas Instruments, Designing and Manufacturing with TI's X2SON Packages application note

8.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

8.3 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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8.4 Trademarks

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8.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

8.6 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

9 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision * (May 2022) to Revision A (October 2025)

Page

- Updated the numbering format for tables, figures, and cross-references throughout the document......
- Added Input and Output LVCMOS Level Translations With Operating Frequency Range table to Description 8

10 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

www.ti.com 21-May-2025

PACKAGING INFORMATION

Orderable part number	Status	Material type	Package Pins	Package qty Carrier	RoHS	Lead finish/ Ball material	.		Part marking (6)
CDCBT1001DPWR	Active	Production	X2SON (DPW) 5	3000 LARGE T&R	Yes	NIPDAUAG	Level-1-260C-UNLIM	-40 to 85	ВТ
CDCBT1001DPWR.B	Active	Production	X2SON (DPW) 5	3000 LARGE T&R	-	NIPDAUAG	Level-1-260C-UNLIM	-40 to 85	BT

⁽¹⁾ Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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⁽²⁾ Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

⁽⁴⁾ Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

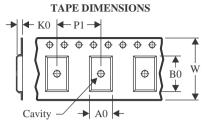
⁽⁶⁾ Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

PACKAGE MATERIALS INFORMATION

www.ti.com 22-Nov-2024

TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

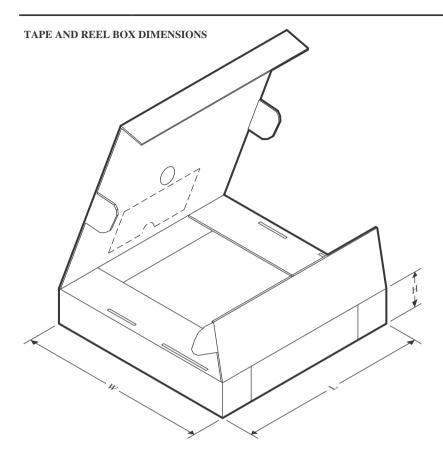


*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CDCBT1001DPWR	X2SON	DPW	5	3000	178.0	8.4	0.91	0.91	0.5	2.0	8.0	Q3

PACKAGE MATERIALS INFORMATION

www.ti.com 22-Nov-2024



*All dimensions are nominal

Ì	Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
ı	CDCBT1001DPWR	X2SON	DPW	5	3000	205.0	200.0	33.0



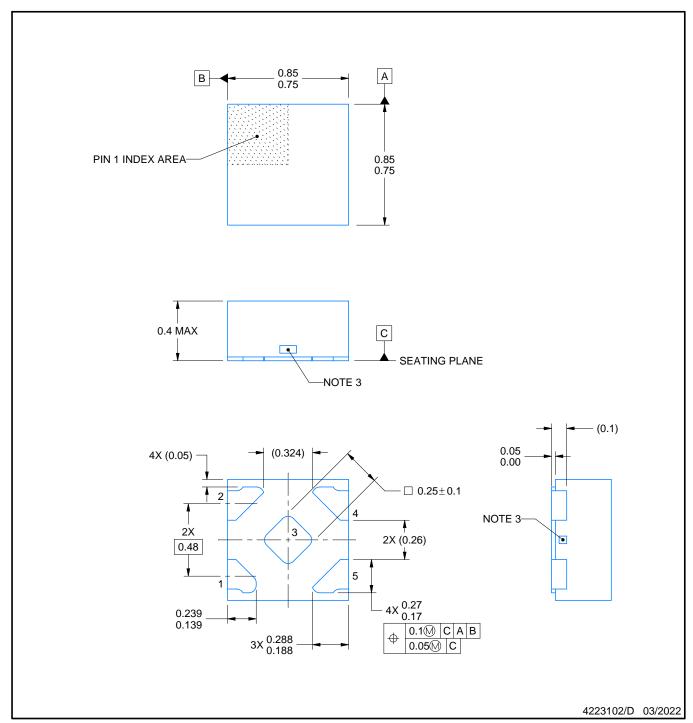
Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.

4211218-3/D





PLASTIC SMALL OUTLINE - NO LEAD



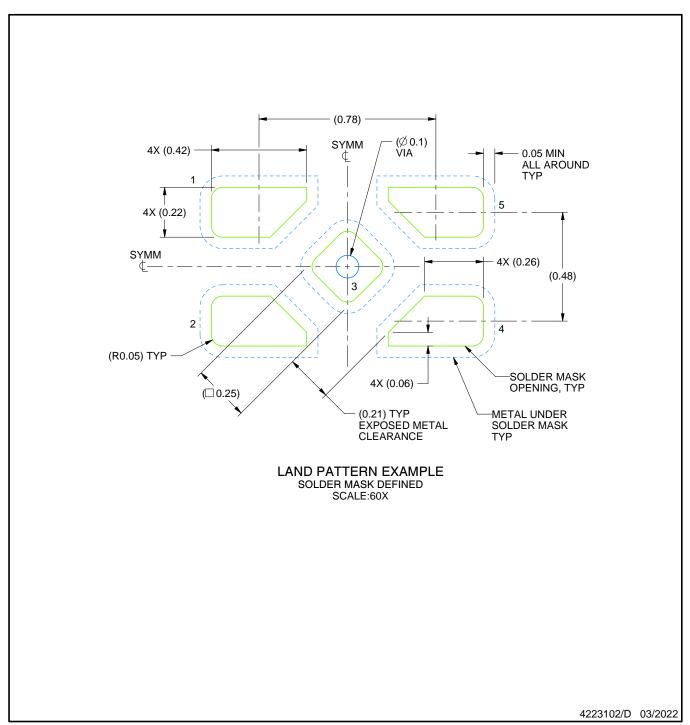
NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.
- 3. The size and shape of this feature may vary.



PLASTIC SMALL OUTLINE - NO LEAD

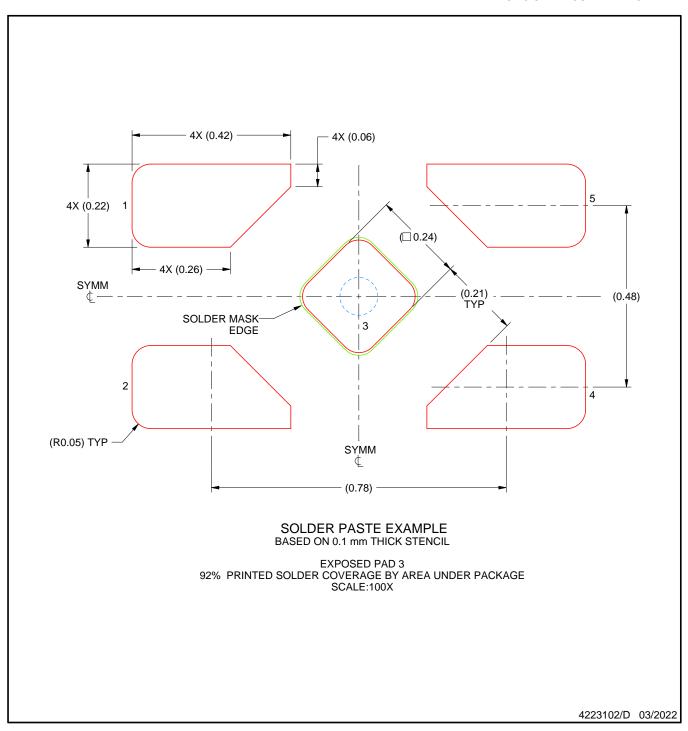


NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, refer to QFN/SON PCB application note in literature No. SLUA271 (www.ti.com/lit/slua271).



PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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